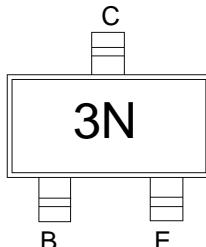
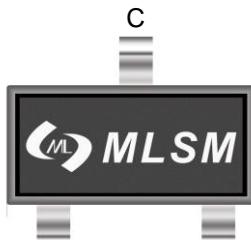


Features

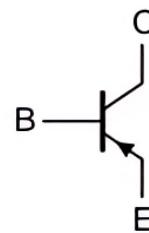
- Epitaxial Planar Die Construction
- Complementary NPN Type Available
- Also Available in Lead Free Version



Marking and pin assignment



SOT-523 top view



Schematic diagram



Halogen-Free

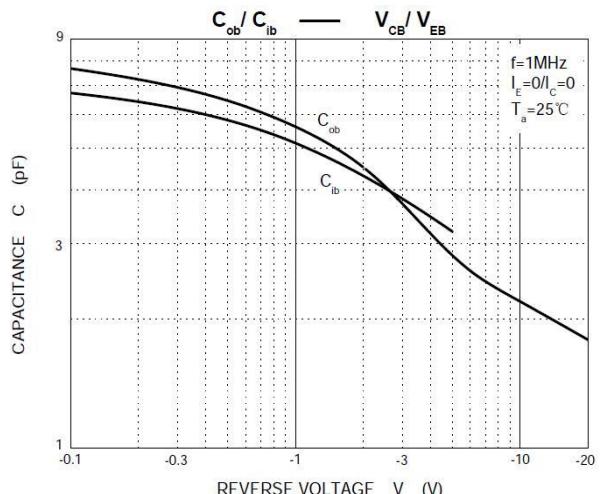
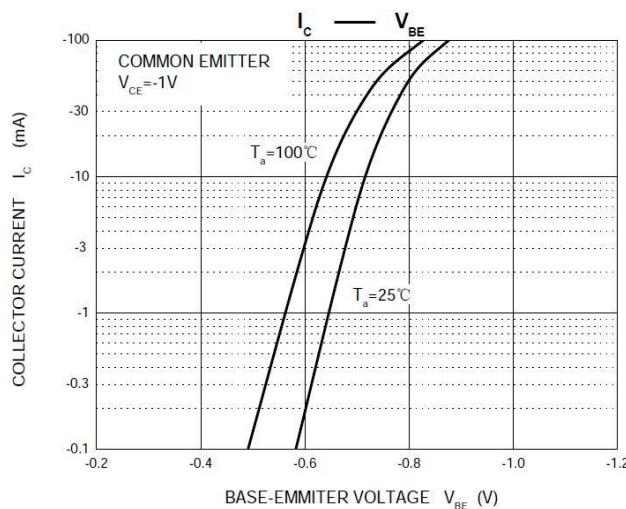
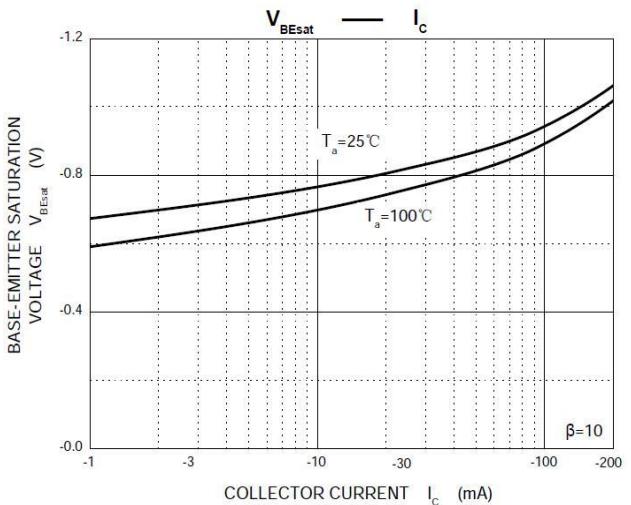
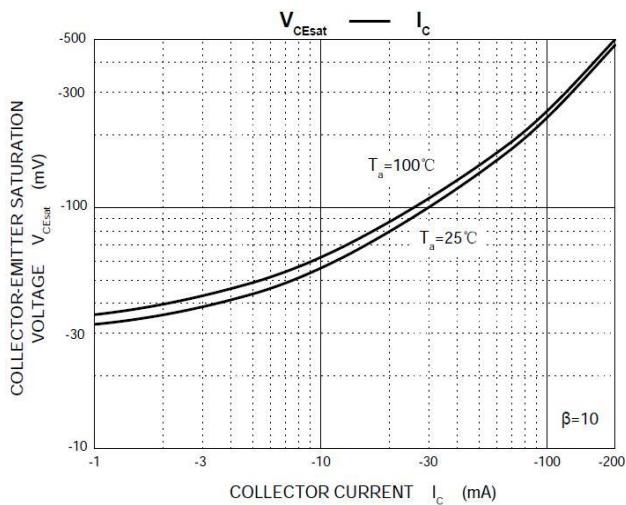
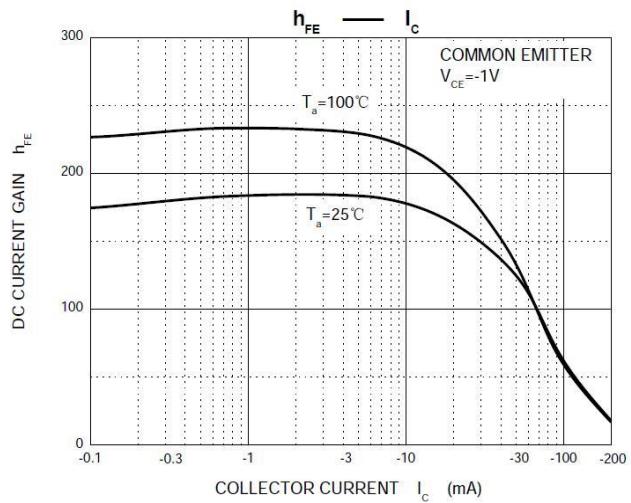
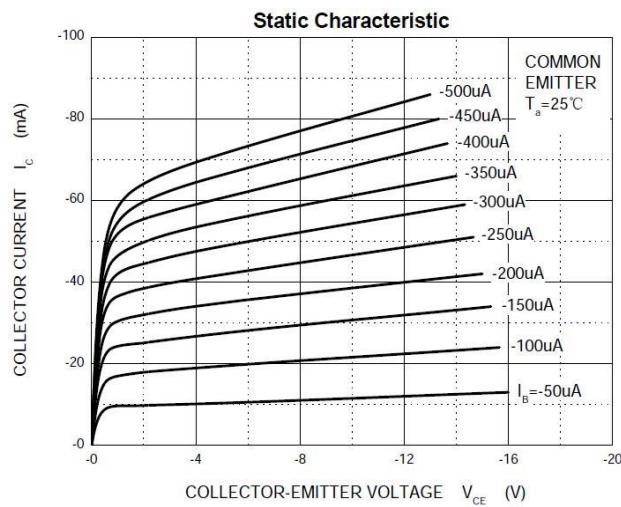
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

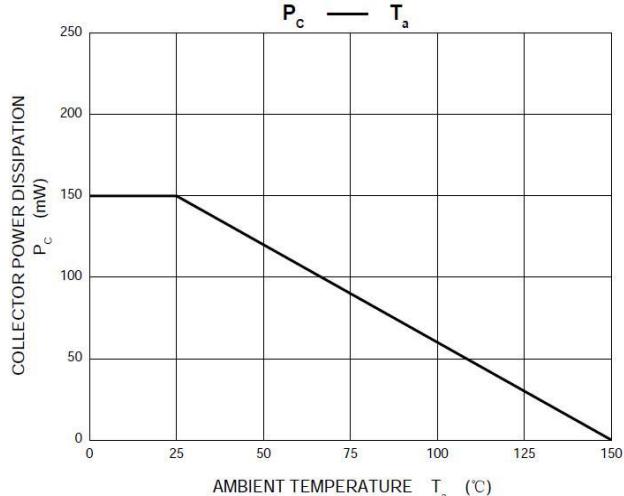
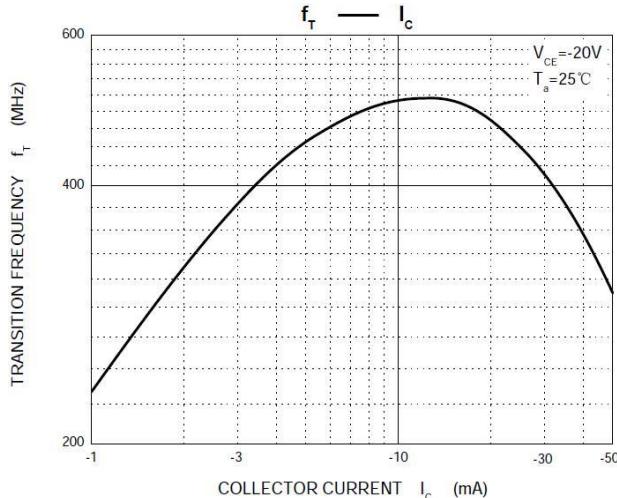
Symbol	Parameter	Limit	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-200	mA
P _C	Power Dissipation	150	mW
R _{θJA}	Thermal Resistance Junction to Ambient	833	°C/W
T _J , T _{STG}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-10μA, I _E =0	-40	--	--	V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, I _B =0	-40	--	--	V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10μA, I _C =0	-5	--	--	V
I _{CBO}	Collector cut-off current	V _{CB} =-40V, I _E =0	--	--	-0.1	μA
I _{CEX}	Collector cut-off current	V _{CE} =-30V, V _{EB(off)} =-3V	--	--	-0.05	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V, I _C =0	--	--	-0.1	μA
<i>h</i> _{FE1}	DC current gain	V _{CE} =-1V, I _C =-0.1mA	60	--	--	
<i>h</i> _{FE2}		V _{CE} =-1V, I _C =-1mA	80	--	--	
<i>h</i> _{FE3}		V _{CE} =-1V, I _C =-10mA	100	--	300	
<i>h</i> _{FE4}		V _{CE} =-1V, I _C =-50mA	60	--	--	
<i>h</i> _{FE5}		V _{CE} =-2V, I _C =-100mA	30	--	--	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-10mA I _B =-1mA	--	--	-0.25	V
		I _C =-50mA I _B =-5mA	--	--	-0.4	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =-10mA I _B =-1mA	-0.65	--	-0.85	V
		I _C =-50mA I _B =-5mA	--	--	-0.95	V
f _T	Transition frequency	V _{CE} =-20V, I _C =-10mA, f=100MHz	250	--	--	MHz
C _{obo}	Output capacitance	V _{CB} =-5V, I _E =0, f=1MHz	--	--	4.5	pF
C _{ib}	Input capacitance	V _{EB} =-0.5V, I _C =0, f=1MHz	--	--	10	pF
NF	Noise figure	V _{CE} =-5V, I _C =0.1mA	--	--	4	dB
t _d	Delay time	V _{CC} =-3V, V _{BE(OFF)} =-0.5V	--	--	35	ns
t _r	Rise time	I _C =-10mA, I _{B1} =-1mA	--	--	35	ns
t _s	Storage time	V _{CC} =-3V, I _C =-10mA, I _{B1} =I _{B2} =-1mA	--	--	225	ns
t _f	Fall time		--	--	75	ns

Typical Operating Characteristics

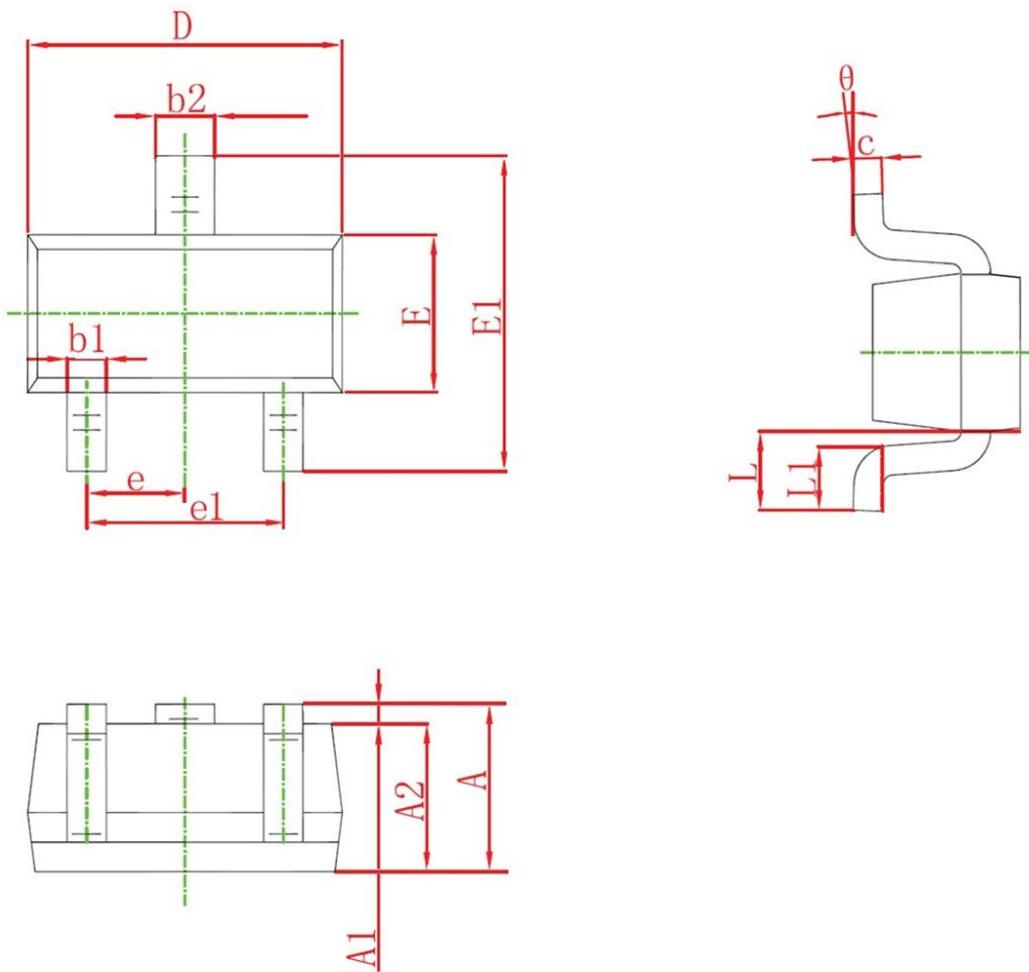




Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MMBT3906T	SOT-523	3N	3,000	45,000	180,000	7"reel

SOT-523 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500TYP		0.020TYP	
e1	0.900	1.100	0.035	0.043
L	0.400REF		0.016REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°